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1. **Imaging of retina cellular and subcellular structures using ptychographic hard X-ray tomography**
Valérie Panneels, Ana Diaz, Cornelia Imsand, Manuel Guizar-Sicairos, [Elisabeth Müller](#), Anne Greet Bitterman, Takashi Ishikawa, Andreas Menzel, Andres Kaech, Mirko Holler, Christian Grimm, Gebhard Schertler
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Elena Marelli, Jaume Gazquez, Emiliya Poghosyan, [Elisabeth Müller](#), Dariusz J. Gawryluk, Ekaterina Pomjakushina, Denis Sheptyakov, Cinthia Piamonteze, Dino Aegerter, Thomas J. Schmidt, Marisa Medarde, and Emiliana Fabbri
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3. **Pt catalytic effects on the corrosion and hydrogen chemisorption properties of Zircaloy-2**
Sriharitha Rowthu, Pascal V. Grundler, [Elisabeth Müller](#), Stefan Ritter
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4. **Design guidelines for an electron diffractometer for structural chemistry and structural biology**
Jonas Heidler, Radosav Pantelic, Julian T. C. Wennmacher, Christian Zaubitzer, Ariane Fecteau-Lefebvre, Kenneth N. Goldie, [Elisabeth Müller](#), Julian J. Holstein, Eric van Genderen, Sacha De Carlo and Tim Gruene
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5. **Three-dimensional imaging of integrated circuits with macro- to nanoscale zoom**
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6. **Ferroelectric Self-Poling in GeTe Films and Crystals**
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7. **Multiferroic phase diagram of E-type RMnO₃ films studied by neutron and x-ray diffraction**
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9. **Combustion generated nanomaterials: online characterization via an ICP-MS based technique. Part II: resolving power for heterogeneous matrices**
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11. **Rapid Structure Determination of Microcrystalline Molecular Compounds Using Electron Diffraction**
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12. **High-resolution, Non-destructive X-ray Tomography**
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13. **Resonant Ptychographic Tomography Facilitates Three-Dimensional Quantitative Colocalization of Catalyst Components and Chemical Elements**
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